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PATENT APPLICATION

RESPONSE UNDER 37 CFR §1.116

EXPEDITED PROCEDURE

TECHNOLOGY CENTER ART UNIT 2811

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

RECEIVED

APR 18 2002

TECHNOLOGY CENTER 2800

In re the Application of

Tomoyoshi KUSHIDA

Group Art Unit: 2811

Application No.: 09/435,766

Examiner: S. Loke

Filed: November 8, 1999

Docket No.: 104361

For: SEMICONDUCTOR DEVICE

AMENDMENT AFTER FINAL REJECTION UNDER 37 CFR §1.116

Director of the U.S. Patent and Trademark Office  
Washington, D.C. 20231

Sir:

In reply to the Office Action mailed January 18, 2002, please amend the above-identified application as follows:

IN THE CLAIMS:

Please replace claims 1, 4, 12, 22-23, 26 and 28-30 as follows:

1. (Three Times Amended) A bipolar semiconductor device comprising:

a drain electrode;

a drain region having a first conductive type and disposed on the drain

electrode;

a drift region having a second conductive type different from the first

conductive type of the drain region and disposed on the drain region;

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sub E7